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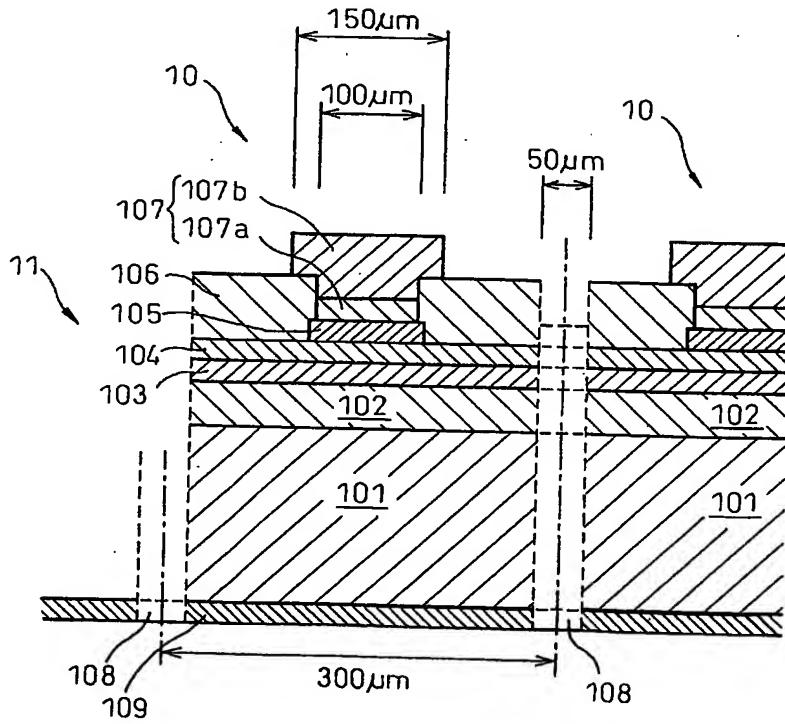
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(54) Title: BORON PHOSPHIDE-BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE AND PRODUCTION METHOD THEREOF



(57) Abstract: A boron phosphide-based semiconductor light-emitting device, comprising: a crystalline substrate; a first semiconductor layer formed on said crystalline substrate, said first semiconductor layer including a light-emitting layer, serving as a base layer and having a first region and a second region different from the first region; a boron phosphide-based semiconductor amorphous layer formed on said first region of said first semiconductor layer, said boron phosphide-based semiconductor amorphous layer including a high-resistance boron phosphide-based semiconductor amorphous layer or a first boron phosphide-based semiconductor amorphous layer having a conduction type opposite to that of said first semiconductor layer; a pad electrode formed on said high-resistance or opposite conductivity-type boron phosphide-based semiconductor amorphous layer for establishing wire bonding; and a conductive boron phosphide-based crystalline layer formed on said second region of said first semiconductor layer, said conductive boron phosphide-based crystalline layer extending optionally to a portion of said pad electrode above the bottom of said pad electrode.

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portion of said boron phosphide-based semiconductor amorphous layer, wherein said pad electrode is in contact with said boron phosphide-based semiconductor crystalline layer at a portion of said pad electrode above the bottom of said pad electrode.



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